# UP05C8B

# Silicon NPN epitaxial planar type (Tr) Silicon epitaxial planar type (CCD load device)

For CCD output circuits

### ■ Features

- Two elements incorporated into one package (Tr + CCD load device)
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.

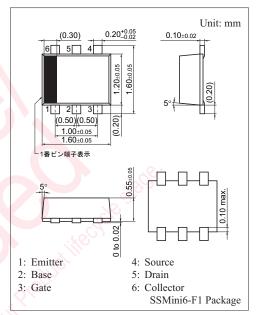
### ■ Basic Part Number

• 2SC3931 + CCD load device

# ■ Absolute Maximum Ratings $T_a = 25$ °C

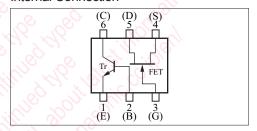
Parameter		Symbol	Rating	Unit	
Tr	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	30	v	
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	20	) V	
	Emitter-base voltage (Collector open)	$V_{\mathrm{EBO}}$	3	V	
	Collector current	$I_{C}$	15	mA	
CCD	Eliming element voltage		40	S V	
load device	Limiting element current	I <sub>max</sub>	.10	mA	
Overall	Total power dissipation *	$P_{T}$	125	mW	
	Junction temperature	Tj	125	<b>€</b>	
	Storage temperature	T <sub>stg</sub>	-55 to +125	°C	

Note) \* : Measuring on substrate at 17 mm  $\times$  10 mm  $\times$  1 mm



# Marking Symbol: 4F

# Internal Connection



# ■ Electrical Characteristics $T_a = 25$ °C±3°C

#### • Tr

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_C = 10 \mu A, I_E = 0$	30			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_E = 10 \ \mu A, I_C = 0$	3			V
Base-emitter voltage	V <sub>BE</sub>	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA}$		720		mV
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 6 \text{ V}, I_C = 1 \text{ mA}$	65		160	_
Reverse transfer capacitance (Common emitter)	C <sub>re</sub>	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 10.7 \text{ MHz}$		0.8		pF
Transition frequency	$f_T$	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 200 \text{ MHz}$		640		MHz
Noise figure	NF	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$		3.3		dB
Power gain	$G_{P}$	$V_{CB} = 6 \text{ V}, I_{E} = -1 \text{ mA}, f = 100 \text{ MHz}$		24		dB

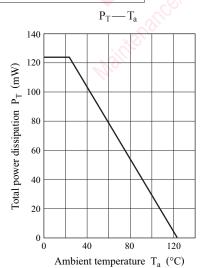
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

## • CCD Load Device

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Pinchi off current	$I_{P}$	$V_{DS} = 10 \text{ V}, V_G = 0$	3.5		5.5	mA
Output impedance	Z <sub>O</sub>	$V_{DS} = 10 \text{ V}, V_{G} = 0$		0.05		ΜΩ

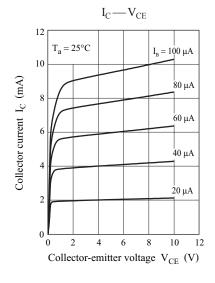
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

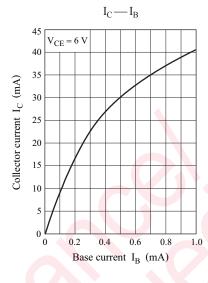
## Common characteristics chart

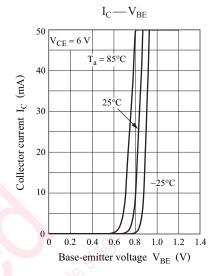


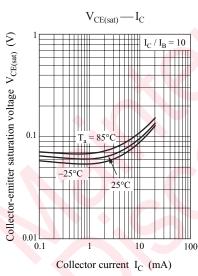
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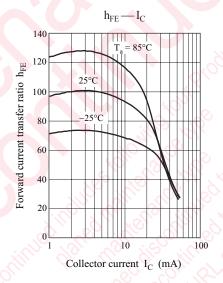
# Characteristics charts of Tr



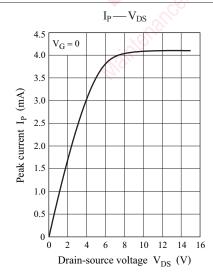








## Characteristics charts of CCD load device



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